

Manufacturing Issues with Current CMP Ring Technology: Tolerance

- Poor consistency of manufactured dimensional tolerances
 - Change in tolerance over time (creep)
 - Notch wear on inner ring diameter
- Dimensional inconsistencies lead to decreased yields and lower plant efficiency
 - Increased wafer breakage (slippage)
 - Degraded process consistency (WIWNU)
 - Increased cost
 - Non-optimized tool utilization
 - Increased carrier rebuilds
 - Test wafer usage

Manufacturing Issues with Current CMP Ring Technology: Wear

- Poor choice of materials of construction
 - Sub-optimal wear characteristics per application
 - Variability in wear rate for dielectric, tungsten and copper
 - Variability in raw material source
 - Results in large variation in expected ring lifetime
- Material choice key for low cost of ownership (CoO)
 - Frequent and expensive ring changes
 - Cost of ring
 - Tool downtime to for ring installation
 - High CoO
 - Poor defectivity due to plastic extrusion variations
 - Voids
 - Non-homogeneous materials (density)
 - Variable wear and shedding

Demonstrated Commercial Successes

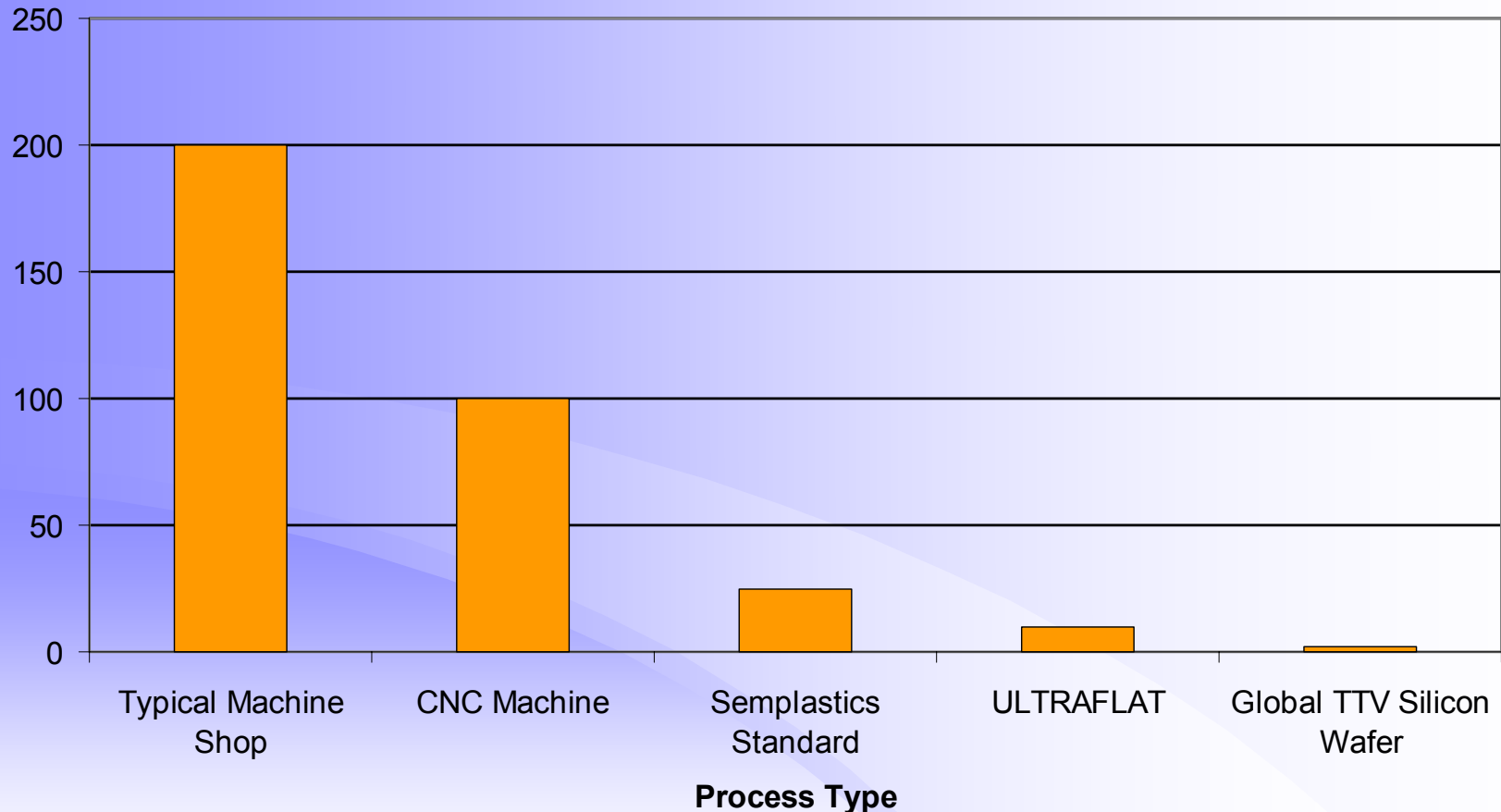
- Eliminated Speedfam CMP V ring wafer breakage issue for tungsten CMP
- Reduced edge wear on Ebara platform by 8X over OEM ring
- Improved CoO of Strasbaugh rings by 66% over previous second source supplier
- Delivered a 2.5X improvement in ring life on IPEC 472 platform over OEM solution

Semplastics' World-Class Plastics Capability

- ULTRAFLAT™ -Semplastics' proprietary technology
 - Holds flatness and parallelism of a specified dimension in a mounted and fixed position
 - 10 microns maximum for 200mm applications
 - 15 microns maximum for 300mm applications
 - All CMP rings are manufactured with ULTRAFLAT™ technology
- Superior plastics knowledge allows for optimizing both the machining and wear properties
 - Different plastics need variations in machining to achieve ultra-precision metrics
 - Semplastics has the experience needed to machine numerous types of plastics to these specifications
 - Wear properties are controlled by the choice of materials
 - Different CMP processes have variable wear rates on ring plastic
 - Semplastics can optimize the material choice to reduce wear and CoO
- Superior quality control for ring manufacture
 - Identify and measure each ring
 - Ring I.D., thickness, parallelism, flatness all QC controlled and traceable

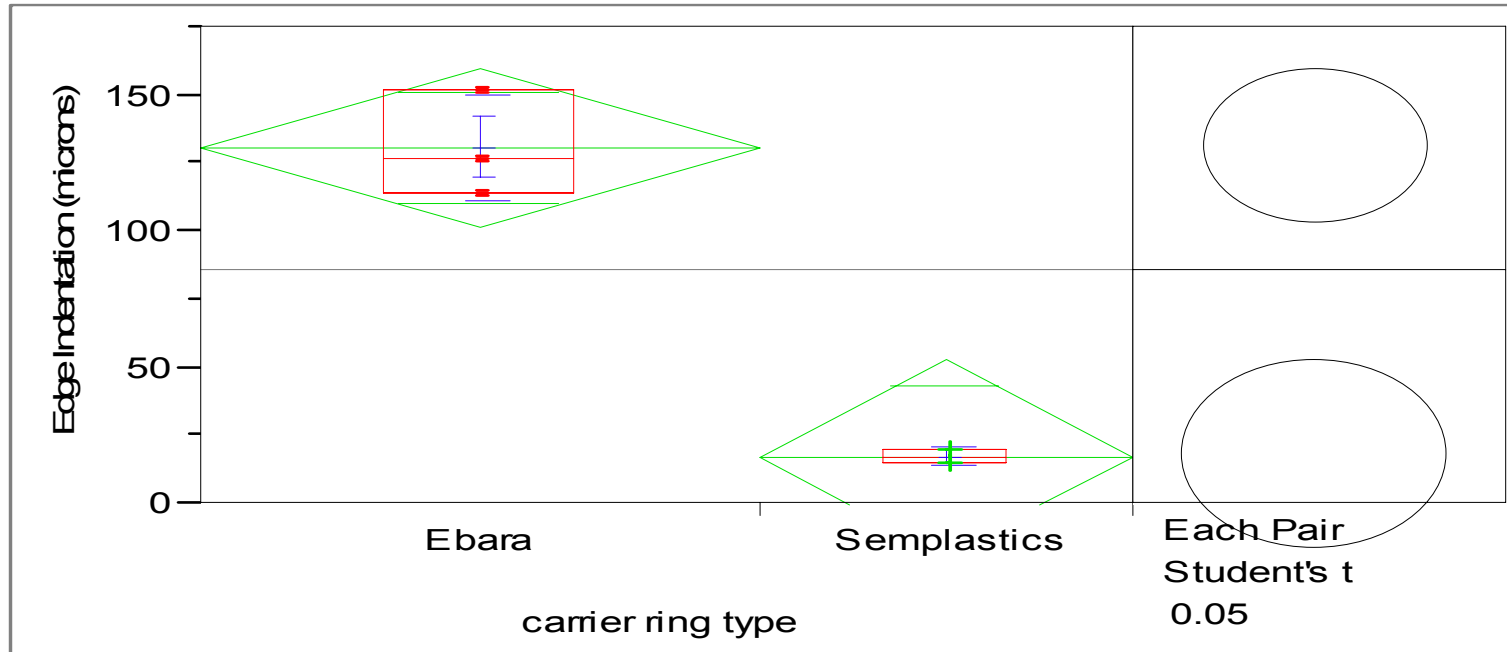
Example of ULTRAFLAT™ Ultra-Precision Plastic Fabrication

Flatness and Parallelism Tolerances(Microns)



Ebara Carrier Ring Inner Edge Indentation Comparison

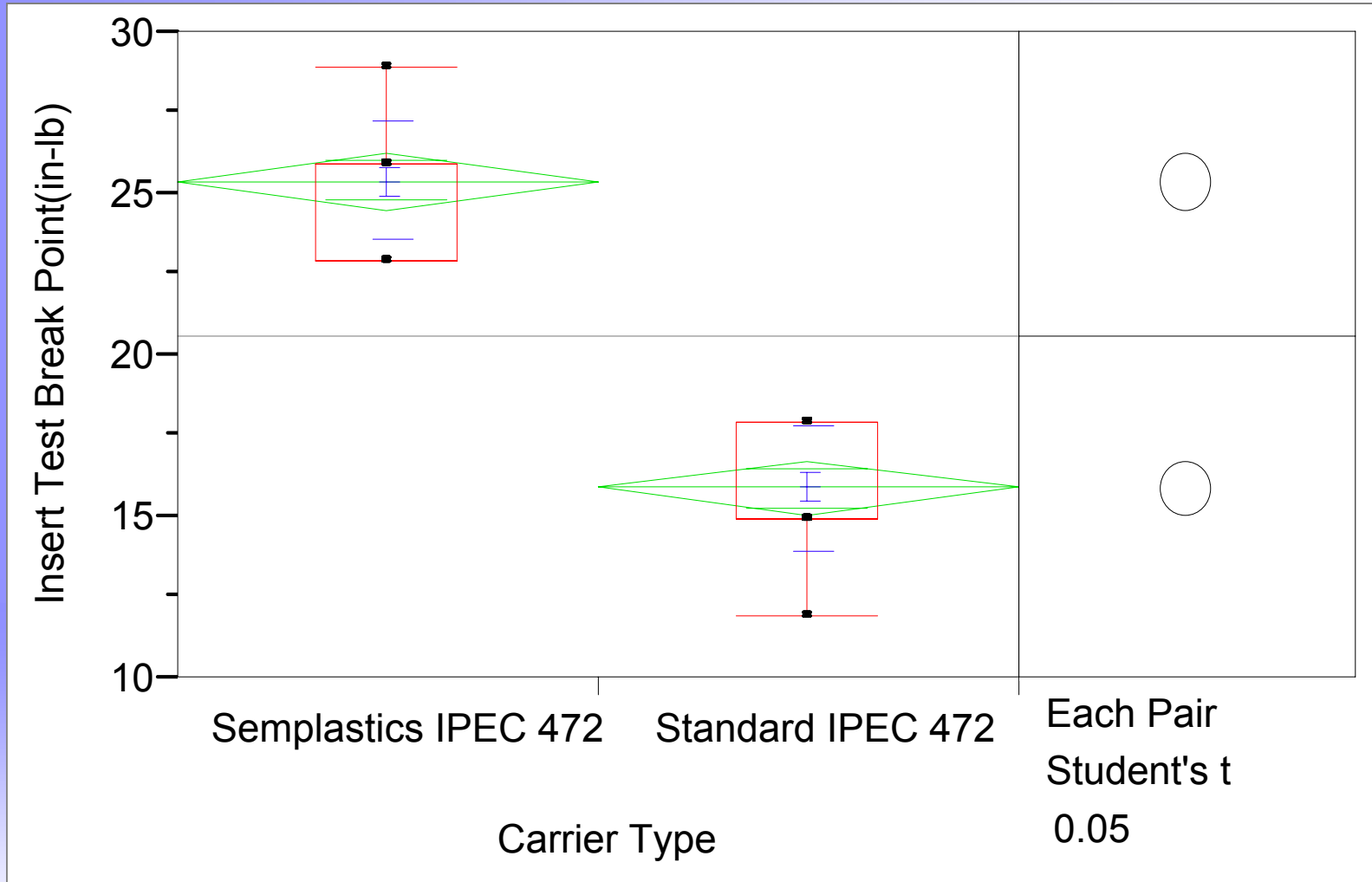
Oneway Analysis of Edge Indentation (microns) By carrier ring type



Means and Std Deviations

Level	Number	Mean	Std Dev	Std Err Mean	Lower 95%	Upper 95%
Ebara	3	131.000	19.3132	11.150	83.02	178.98
Semplastics	2	17.500	3.5355	2.500	-14.27	49.27

SF-IPEC Ring Insert Improvement



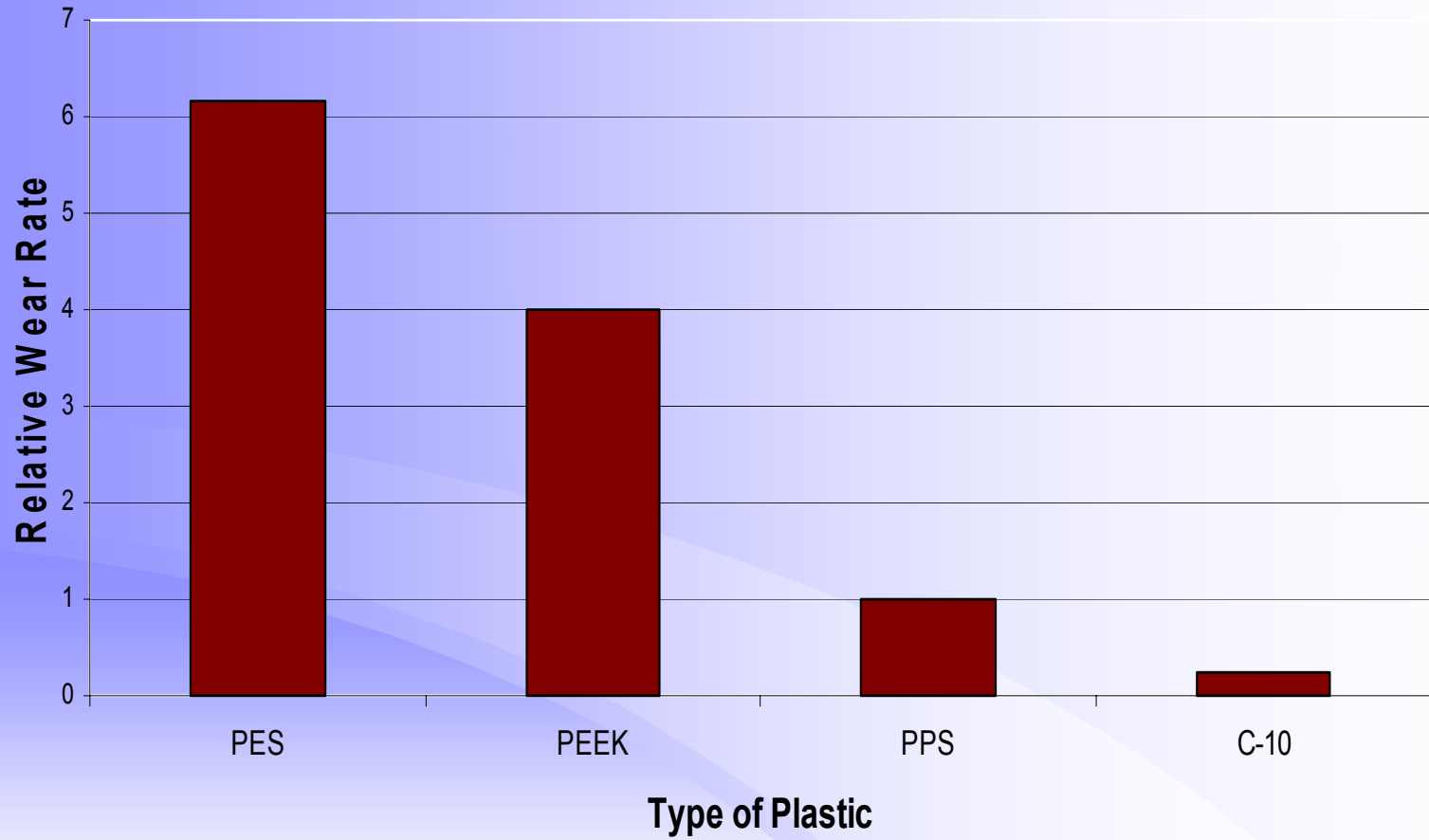
Comparison of Semplastics' C-10™ Material to Typical Ring Plastics

Plastic*	Specific Gravity	Tensile Strength (PSI)	Tensile Mod. Of Elasticity (PSI)	Sheer Strength (PSI)	Hard Shore D	COF	Relative Wear Rate
PC	1.20	10,500	320,000	13,000	80	N/A	N/A
PET	1.41	12,400	460,000	8,000	87	0.20	1.20
PES	1.37	12,200	385,000	9,000	80	N/A	3.30
PEEK	1.31	16,000	500,000	8,000	85	0.40	1.52
PPS	1.35	13,500	500,000	9,000	85	0.40	1.00
C-10™	1.42	10,500	420,000	9,000	87	0.21	0.35

*The plastics described above include the following: PC (polycarbonate), PET (Polyethyleneterephalate), PES (Polyethersulfone), PEEK (Polyetheretherketone), PPS (Polyphenylsulfide), and C-10™ (Trademark of Semplastics)

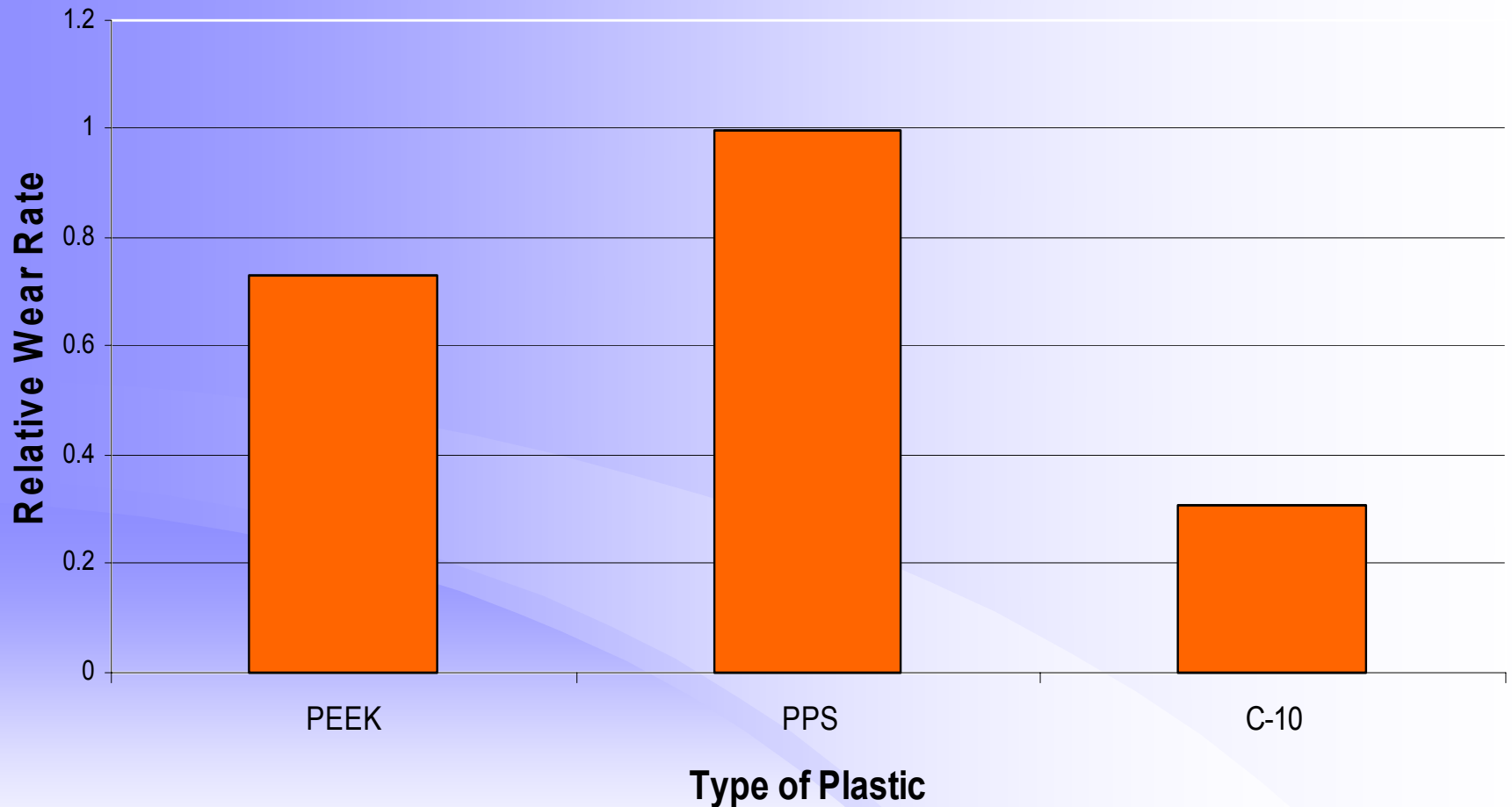
Tungsten Slurry Ring Wear Data

Tungsten Slurry Relative Wear Rate



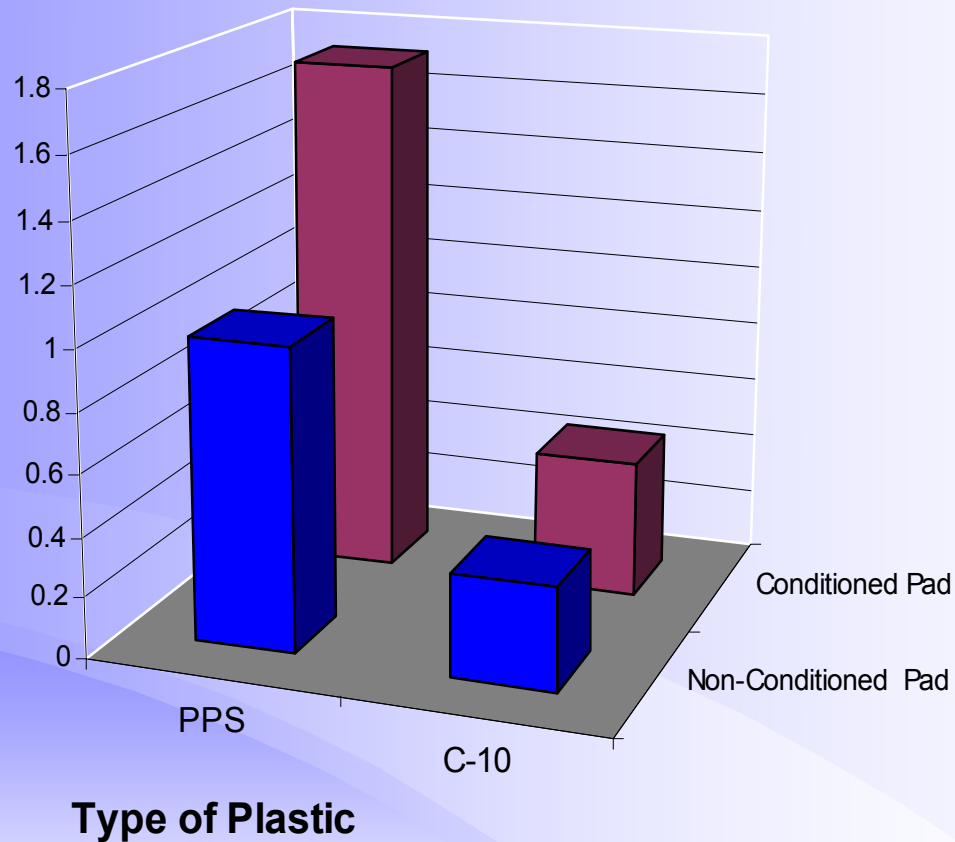
Copper Slurry Ring Wear Data

Copper Slurry Relative Wear Rate



Dielectric Slurry Wear Data

Wear Comparison- Oxide Slurry Relative to Unconditioned PPS



Customer Partnering Success

IPEC 472

- Issues identified as premature insert failures, warpage and premature cracking
 - Superior insert engineering coupled with ULTRAFLAT™ manufacturing process solved issue
- Ring performance demonstrated at over 20,000 wafer passes for customer's tungsten CMP process
- Demonstrated over a 2.5X extension in ring lifetime compared to OEM product
- Semplastics engineered solution exceeded customer expectations

Normalized CoO Example

Applied Materials

Process Technology	Ring Life			Carrier Cost/Wafer Pass			Total Cost/Wafer Pass		
	OEM	Semplastics	Δ	OEM	Semplastics	Δ	OEM	Semplastics	Δ
Dielectric	0.3	0.9	300%	0.14	0.05	66.7%	1.0	0.83	17.3%
Tungsten	0.5	1.5	300%	0.11	0.04	63.6%	1.2	1.05	12.5%
Copper	1.0	3.0	300%	0.06	0.02	66.7%	1.3	1.18	9.2%

Assumptions:

- 3X improvement in ring lifetime
- 10 test wafers/ carrier rebuild
- 10X improvement in wafer breakage rate
- No difference in electrical yield accounted for

Example Savings on Annual Spend Applied Materials

Assumption: 4 level metal process (1 STI, 4 ILD, 4 W)
4,000 wafers/week (36,000 wafer passes)
Net usage: 936 dielectric/year, 562 W/year
Annual spend on OEM (@\$800/ring) = \$1,198,000
Annual spend on Semplastics (@ 3x life) = \$400,000

Net Annual Spend Reduction = \$ 798,000

Example Savings on Wafer Breakage Applied Materials

Assumption: 4 level metal process (1 STI, 4 ILD, 4 W)
4,000 wafers/week (36,000 wafer passes)
Net yield 200 die/wafer @ \$20 ASP = \$4,000/wafer
Semplastics' ring provides 10X mechanical breakage
improvement (1/100,000 Vs 1/10,000 POR)
Net improvement of 3.24 wafers lost/week
Annual yield of 168 fewer wafer breakages/year

Net Annual Yield Improvement = \$672,000

Summary

- Semplastics brings a unique combination of machining expertise and materials knowledge to the high-tech marketplace
- Large depth of IC industry experience and perspective (65+ years)
- Strong history of supply to demanding IC customers
 - Demonstrated capacity and upside swing reserve capacity
- Strong IP position
 - ULTRAFLAT™, C-10™ technologies
 - All-plastic AMAT ring
- Demonstrated improvements in CoO and wafer breakage
 - Demonstrated 2.5X lifetime increase with potential for 5X
 - Ability to significantly reduce customer's CoO
 - Proven 66% CoO reduction at customer site
 - Significant reduction in ring related wafer breakage
 - Potential to improve WIWNU and copper defectivity